AMENDMENTS TO THE SPECIFICATION

Please amend paragraph [0012] as follows:

In order to achieve the objects mentioned above, there is provided in accordance with a present invention a diboride single crystal substrate that is a single crystal substrate of diboride XB_2 (where X is either Zr or Ti), characterized in that the substrate is facially oriented in a (0001) plane, has an orientation flat exhibiting a (10-10) or (11-20) plane and has a thickness of 0.1 mm or less whereby the substrate can be cleaved in a (10-10) plane. ~~The diboride XB_2 single crystal substrate may have an orientation flat indicating a (10-10) or (11-20) plane.~~

Please amend paragraph [0013] as follows:

~~The present invention also provides a semiconductor laser diode, characterized in that it is formed on a substrate of diboride XB_2 single crystal (where X is either Zr or Ti) that is facially oriented in a (0001) plane of the single crystal.~~ The present invention also provides a semiconductor laser diode having a multilayered active layer is formed on a substrate of diboride XB_2 single crystal (where X is either Zr or Ti) which is facially oriented in a (0001) plane of the single crystal, characterized in that a pair of opposed end faces defining a semiconductor laser light resonator in the multilayered active layer and opposed end faces of the diboride XB_2 single crystal substrate are each constituted by a cleavage face oriented parallel to a (10-10) plane of the diboride XB_2 single crystal substrate.

Please amend paragraph [0014] as follows:

~~Preferably, the semiconductor laser diode formed on the diboride XB_2 single crystal substrate has a multilayered active layer, the diboride XB_2 single crystal substrate has cut faces each lying along a (10-10) plane thereof, and the multilayered active layer has a pair of opposed end faces constituting a semiconductor laser light resonator which are formed by cleavage faces lying parallel to the (10-10) plane of the diboride XB_2 single crystal substrate.~~ The diboride XB_2 single crystal substrate may have a thickness of 0.1 mm or less. Also, the diboride XB_2 single crystal substrate may be a ZrB_2 single crystal substrate, and the multilayered active layer of the semiconductor laser diode may comprise a nitride compound semiconductor ($Al_xGa_yIn_zN$ where $x + y + z = 1$).

Please amend paragraph [0016] as follows:

The present invention also provides a semiconductor device that is formed on a substrate of a diboride XB_2 single crystal (where X is Zr or Ti) which is facially oriented in a (0001) plane of the single crystal, ~~characterized in that: the diboride XB_2 single crystal substrate has a pair of cut faces resulting from cutting a said substrate upon scribing it with a diamond pen or the like along a (10-10) plane; and a semiconductor device constituting the device has side faces at least one of which is parallel to the (10-10) plane of the diboride XB_2 single crystal substrate~~ characterized in that those at least at one side of side faces of the diboride XB_2 single crystal substrate and of a device constituting a semiconductor device are constituted by cut faces resulting from cleaving the substrate and the device parallel to a (10-10) plane of the diboride XB_2 single crystal substrate.